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AMENDMENTS TO THE CLAIMS:

*This listing of claims will replace all prior versions, and listings, of claims in the application:*

1-28. (Canceled)

29. (Currently amended) A crystal growth method for adding or crystallizing nitrogen in a crystal supported by a substrate, comprising:

supplying aluminum and ammonium ( $\text{NH}_3$ ) to a surface of the crystal,

wherein addition or crystallization of the nitrogen from the ammonium which is supplied to the surface of the crystal into the surface of the crystal is accelerated by the aluminum supplied to the surface of the crystal, and

wherein the substrate is at a temperature of 450 degrees C or more and less than 640 degrees C when the aluminum and ammonium are supplied.

30. (Previously presented) A crystal growth method according to claim 29, wherein decomposition of ammonium and adsorption of nitrogen on a crystal surface is accelerated by aluminum.

31. (Previously presented) A crystal growth method according to claim 29, wherein the aluminum exists at least in an outermost surface of a growing layer.

32. (Previously presented) A crystal growth method according to claim 29, wherein an amount of nitrogen added to a crystal, a nitrogen composition, an amount of nitrogen adsorbed